

FCH47N60 / FCA47N60 / FCA47N60_F109

600V N-Channel MOSFET

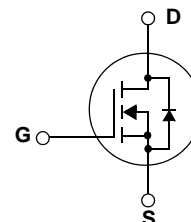
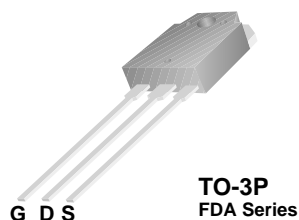
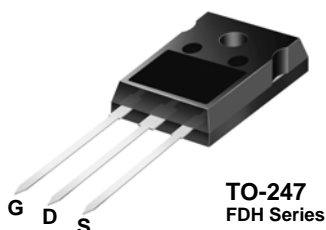
Features

- 650V @T_J = 150°C
- Typ. R_{ds(on)}=0.058Ω
- Ultra low gate charge (typ. Q_g=210nC)
- Low effective output capacitance (typ. C_{oss,eff}=420pF)
- 100% avalanche tested

Description

SuperFET™ is, Fairchild's proprietary, new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.



Absolute Maximum Ratings

Symbol	Parameter	FCH47N60	FCA47N60	Unit
V _{DSS}	Drain-Source Voltage	600		V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	47 29.7		A A
I _{DM}	Drain Current - Pulsed (Note 1)	141		A
V _{GSS}	Gate-Source voltage	± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	1800		mJ
I _{AR}	Avalanche Current (Note 1)	47		A
E _{AR}	Repetitive Avalanche Energy (Note 1)	41.7		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	417 3.33		W W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	--	0.3	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink	0.24	--	
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	41.7	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCH47N60	FCH47N60	TO-247	-	-	30
FCA47N60	FCA47N60	TO-3P	-	-	30
FCA47N60	FCA47N60_F109	TO-3PN	-	-	30

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}, T_J = 25^\circ\text{C}$	600	--	--	V
		$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}, T_J = 150^\circ\text{C}$	--	650	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C	--	0.6	--	V/ $^\circ\text{C}$
BV _{DS}	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 47\text{A}$	--	700	--	V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$	--	--	1	μA
		$V_{DS} = 480\text{V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{V}, V_{DS} = 0\text{V}$	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{V}, V_{DS} = 0\text{V}$	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10\text{V}, I_D = 23.5\text{A}$	--	0.058	0.07	Ω
g _{FS}	Forward Transconductance	$V_{DS} = 40\text{V}, I_D = 23.5\text{A}$ (Note 4)	--	40	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	--	5900	8000	pF
C _{oss}	Output Capacitance		--	3200	4200	pF
C _{rss}	Reverse Transfer Capacitance		--	250	--	pF
C _{oss}	Output Capacitance	$V_{DS} = 480\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	--	160	--	pF
C _{oss eff.}	Effective Output Capacitance	$V_{DS} = 0\text{V to } 400\text{V}, V_{GS} = 0\text{V}$	--	420	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 300\text{V}, I_D = 47\text{A}$ $R_G = 25\Omega$	--	185	430	ns
t _r	Turn-On Rise Time		--	210	450	ns
t _{d(off)}	Turn-Off Delay Time		--	520	1100	ns
t _f	Turn-Off Fall Time		(Note 4, 5)	--	75	160
Q _g	Total Gate Charge	$V_{DS} = 480\text{V}, I_D = 47\text{A}$ $V_{GS} = 10\text{V}$	--	210	270	nC
Q _{gs}	Gate-Source Charge		--	38	--	nC
Q _{gd}	Gate-Drain Charge		(Note 4, 5)	--	110	--
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	47	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	141	A
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 47\text{A}$	--	--	1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0\text{V}, I_S = 47\text{A}$ $di_F/dt = 100\text{A}/\mu\text{s}$ (Note 4)	--	590	--	ns
Q _{rr}	Reverse Recovery Charge		--	25	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 18\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 47\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

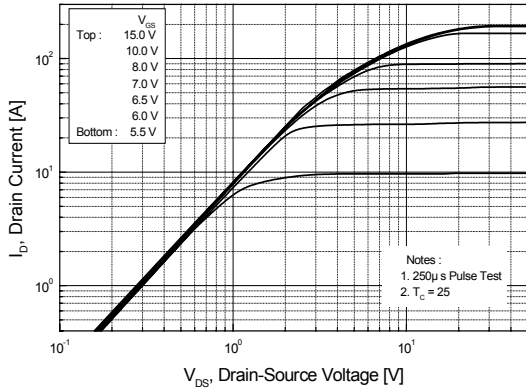


Figure 2. Transfer Characteristics

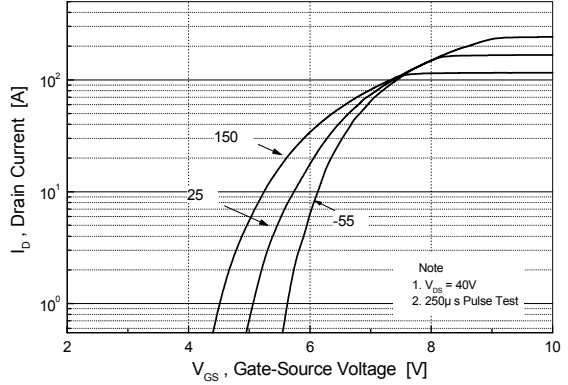


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

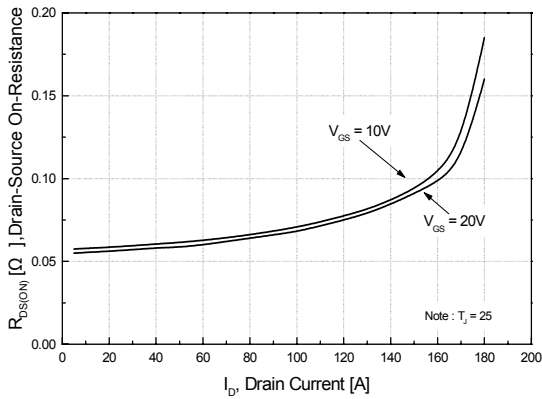


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

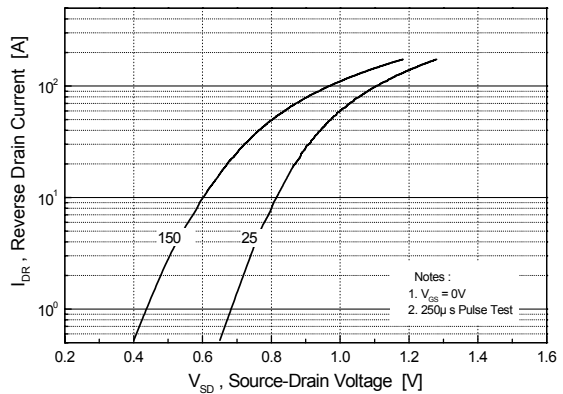


Figure 5. Capacitance Characteristics

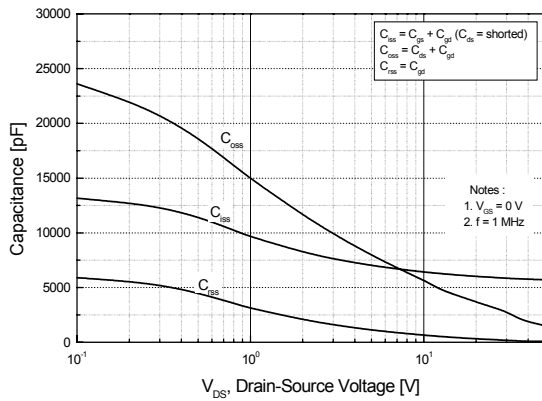
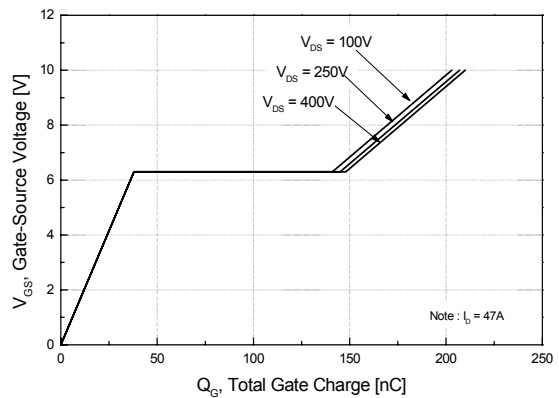


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

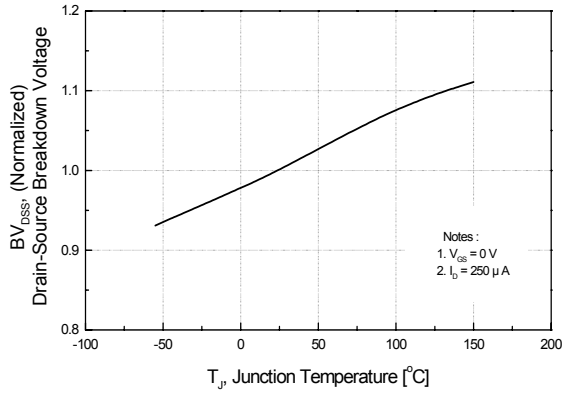


Figure 8. On-Resistance Variation vs. Temperature

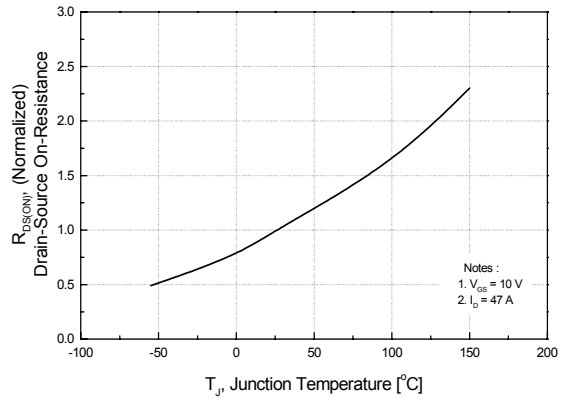


Figure 9. Safe Operating Area

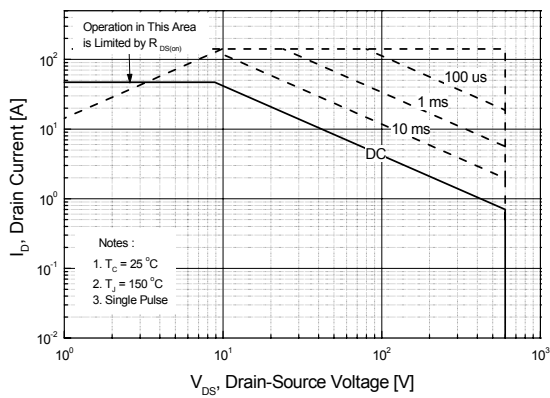


Figure 10. Maximum Drain Current vs. Case Temperature

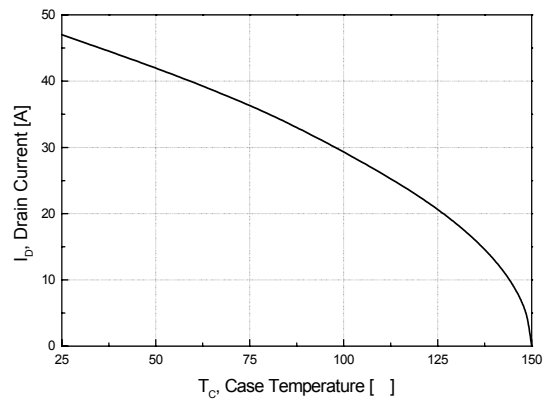
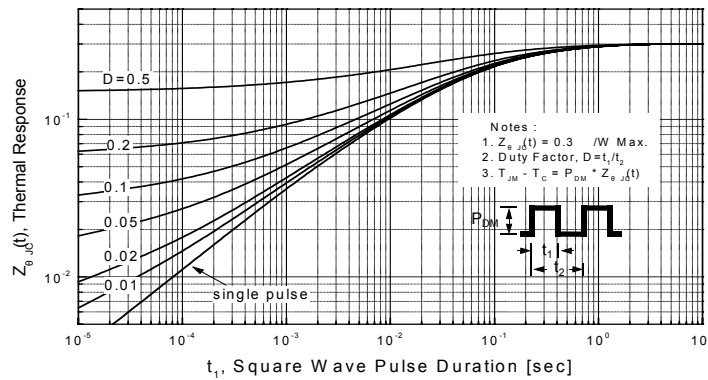


Figure 10. Transient Thermal Response Curve



Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

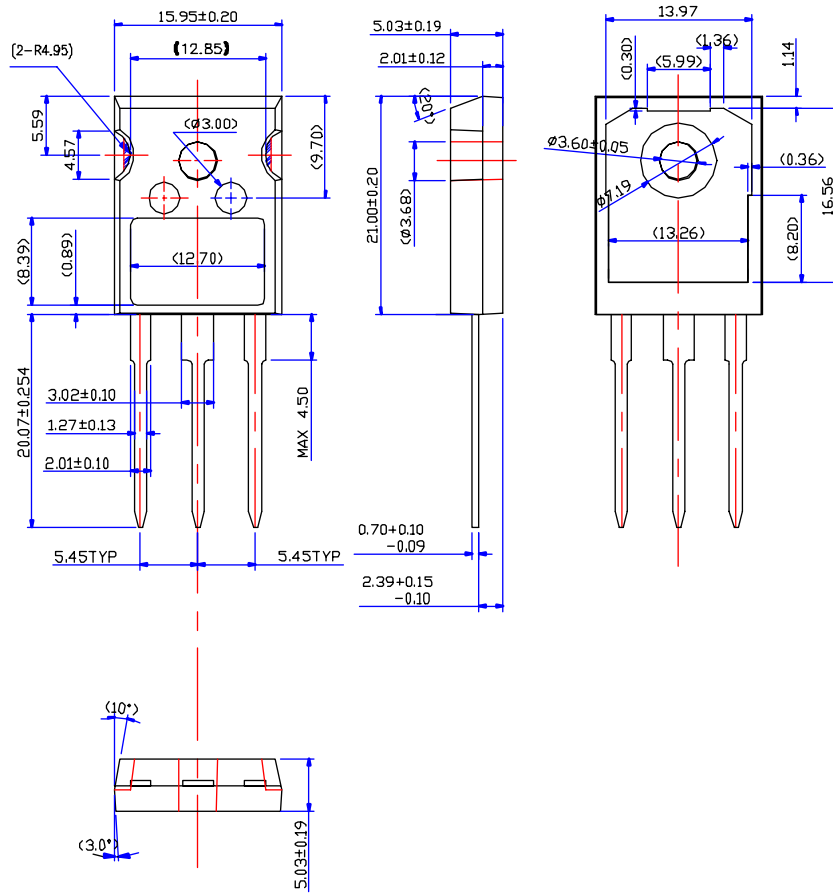


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

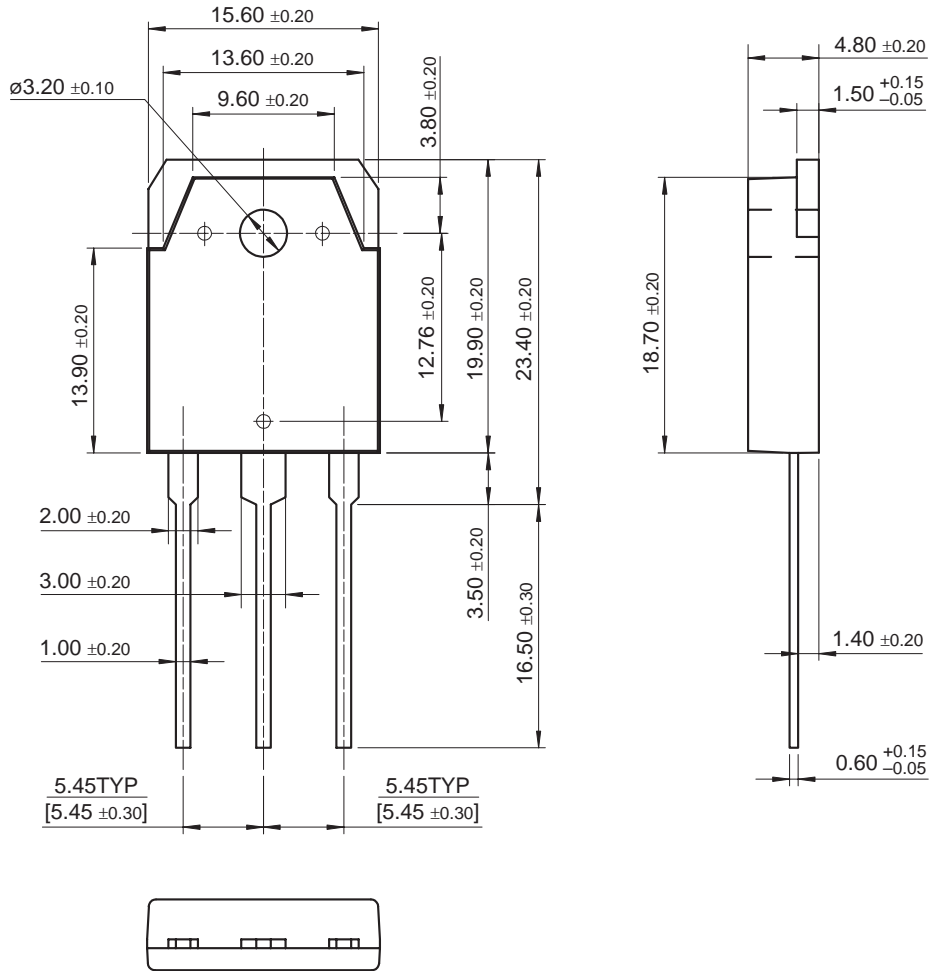
TO-247AD (FKS PKG CODE 001)



Dimensions in Millimeters

Mechanical Dimensions (Continued)

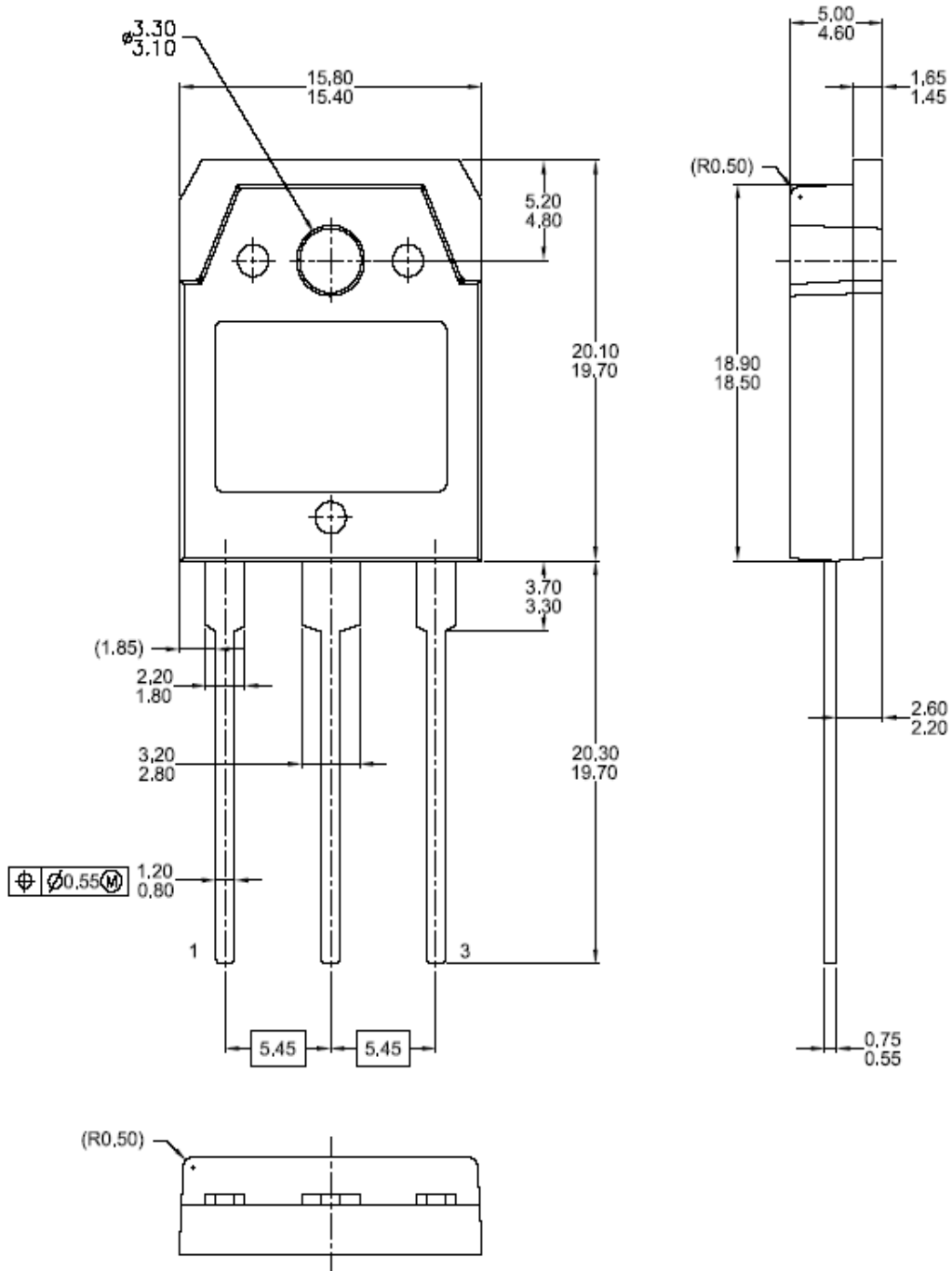
TO-3P



Dimensions in Millimeters

Mechanical Dimensions (Continued)

TO-3PN




Dimensions in Millimeters



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